

lower casing part, in which the pedestal 5 is disposed. The casing 2a of the process chamber 2 has a ceiling, which is formed of an openable or detachable lid 11. The lid 11 has an opening 12 having a size larger than that of the worktable 3 at a position opposite to the worktable 3. A ring showerhead 13 made of quartz is disposed near the opening 12, and is connected to a gas supply section 13a for supplying a process gas containing an oxidizing gas, such as ozone (O<sub>3</sub>). The showerhead 13 is provided with a number of gas spouting holes, which are formed at the bottom to spout a process gas, such as ozone, toward the wafer W on the worktable 3.

**Please amend the paragraph on page 12, beginning at line 24, to read as shown below:**

Then, the wafer W is heated to a predetermined process temperature by the resistance heater 4 disposed in the worktable 3. The process chamber 2 is supplied with ozone gas, i.e., a process gas, while the process chamber 2 is exhausted, so that the interior of the process chamber 2 is kept at a predetermined process pressure. The ozone gas is spouted from the holes of the showerhead 13 toward the wafer W on the worktable 3. At the same time, the UV lamps 17 in the lamp chamber 16 are turned on to emit UV rays. The UV rays are radiated onto the process gas containing ozone as the main component, above the worktable 3 in the process chamber 2. The ozone is decomposed into oxygen and oxygen radicals, due to irradiation with the UV rays. The wafer W on the worktable 3 is subjected to a predetermined process, i.e., oxidation, with the oxygen radicals.